



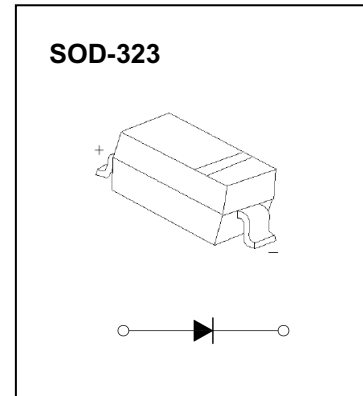
SOD-323 Plastic-Encapsulate Diodes

SD103AWS-SD103CWS SCHOTTKY BARRIER DIODE

FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- Negligible Reverse Recovery Time
- Low Reverse Capacitance

MARKING: SD103AWS: S4
 SD103BWS: S5
 SD103CWS: S6



Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	SD103AWS	SD103BWS	SD103CWS	Unit
Peak Repetitive Peak Reverse Voltage	V_{RRM}				
Working Peak Reverse Voltage	V_{RWM}	40	30	20	V
DC Blocking Voltage	V_R				
RMS Reverse Voltage	$V_{R(RMS)}$	28	21	14	V
Forward Continuous Current	I_{FM}	350			mA
Repetitive Peak Forward Surge Current @t≤1s	I_{FSM}	1.5			A
Power Dissipation	P_d	200			mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	500			°C/W
Junction Temperature	T_j	125			°C
Storage Temperature	T_{STG}	-55~+150			°C

Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	$V_{(BR)R}$	40			V	$I_R=100\mu A$
SD103AWS		30				$I_R=100\mu A$
SD103BWS		20				$I_R=100\mu A$
Forward voltage	V_F			0.37 0.60	V	$I_F=20mA$ $I_F=200mA$
Reverse current	I_{RM}			5.0		μA
SD103AWS						
SD103BWS						
Capacitance between terminals	C_T			50	pF	$V_R=0V, f=1.0MHz$
Reverse recovery time	t_{rr}		10		ns	$I_F=I_R=200mA$ $I_{rr}=0.1I_R, R_L=100\Omega$
SD103CWS						

Typical Characteristics

SD103AWS

